

N-channel 50 V, 2.1 mOhm, 200 A continuous, logic level Application Specific MOSFET in LFPAK56E 26 January 2022

Product data sheet

1. General description

200 Amp continuous current, logic level gate drive, N-channel enhancement mode MOSFET in LFPAK56E package. Part of the ASFETs for Battery Isolation and DC Motor control family and using Nexperia's unique "SchottkyPlus" technology delivers high efficiency and low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. The ASFET is particularly suited to 36 V battery powered applications requiring strong avalanche capability, linear mode performance, use at high switching frequencies, and also safe and reliable switching at high load-current.

2. Features and benefits

- 200 A continuous current capability
- Optimised for 36 V (nominal) battery powered applications
- LFPAK56E low-stress exposed lead-frame for ultimate reliability, optimum soldering and easy solder-joint inspection
- Copper-clip and solder die attach for low package inductance and resistance, and high ID (max) rating
- Qualified to 175 °C
- Avalanche rated, 100% tested
- Low Q_G, Q_{GD} and Q_{OSS} for high efficiency, especially at higher switching frequencies
- Superfast switching with soft body-diode recovery for low-spiking and ringing, recommended for low EMI designs
- Unique "SchottkyPlus" technology for Schottky-like switching performance and low IDSS leakage
- Narrow V_{GS(th)} rating for easy paralleling and improved current sharing
- Very strong linear-mode / safe operating area characteristics for safe and reliable switching at high-current conditions

3. Applications

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- Brushless DC motor control
- Synchronous rectifier in high-power AC-to-DC applications, e.g. server power supplies
- Battery protection and Battery Management Systems (BMS)
- Load switch
- 10 cell lithium-ion battery applications (36 V 42 V)

4. Quick reference data

Table 1. Quick reference data								
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit	
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	55	V	
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	200	А	
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	333	W	
Tj	junction temperature			-55	-	175	°C	

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10	-	1.63	2.1	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.83	2.4	mΩ
Dynamic ch	naracteristics			_		
Q _{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 27 \text{ V}; V_{GS} = 4.5 \text{ V};$ Fig. 12; Fig. 13	-	14	31	nC
Q _{G(tot)}	total gate charge		-	54	84	nC

[1] 200A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		
2	S	source		
3	S	source		D
4	G	gate		
mb	D	mounting base; connected to drain	LFPAK56E; Power- SO8 (SOT1023)	G LFA mbb076 S

6. Ordering information

Table 3. Ordering information

Type number	Package	ackage					
	Name	Description	Version				
PSMN2R0-55YLH	LFPAK56E; Power-SO8	plastic, single-ended surface-mounted package (LFPAK56); 4 leads; 1.27 mm pitch	SOT1023				

7. Marking

Table 4. Marking codes					
Type number	Marking code				
PSMN2R0-55YLH	2H055L				

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	55	V
V _{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ	-	55	V

PSMN2R0-55YLH

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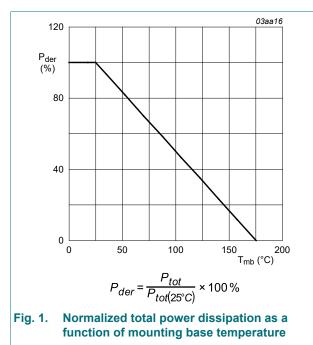
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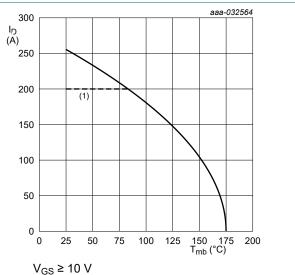
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Parameter	Conditions		Min	Мах	Unit
gate-source voltage			-20	20	V
total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	333	W
drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	200	А
	V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	181	А
peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3		-	1049	А
storage temperature			-55	175	°C
junction temperature			-55	175	°C
peak soldering temperature			-	260	°C
iode	1				
source current	T _{mb} = 25 °C		-	200	А
peak source current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C		-	1049	А
gedness	1				
non-repetitive drain- source avalanche energy	$ \begin{array}{l} I_D = 50 \; A; \; V_sup \leq \; 55 \; V; \; R_GS = 50 \; \Omega; \\ V_GS = 10 \; V; \; T_{j(init)} = 25 \; ^\circC; \; unclamped; \\ t_p = 417 \; \mus \end{array} $	[2]	-	745	mJ
	I_D = 25 A; $V_{sup} \le 55$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; t_p = 1.98 s	[2]	-	1.77	J
non-repetitive avalanche current		[2]	-	115	A
	total power dissipation total power dissipation drain current peak drain current storage temperature junction temperature peak soldering temperature iode source current peak source current gedness non-repetitive drain-source avalanche energy non-repetitive avalanche	$\begin{tabular}{ c c c c } \hline total power dissipation & T_{mb} = 25 °C; Fig. 1 \\ \hline total power dissipation & V_{GS} = 10 V; T_{mb} = 25 °C; $Fig. 2 \\ \hline V_{GS} = 10 V; T_{mb} = 100 °C; $Fig. 2 \\ \hline V_{GS} = 10 V; T_{mb} = 25 °C; $Fig. 3 \\ \hline $torage temperature $ $pulsed; t_p \le 10 μs; T_{mb} = 25 °C; $Fig. 3 \\ \hline $torage temperature $ $peak soldering $ $temperature $ $temperat$	$\begin{tabular}{ c c c c } \hline total power dissipation & T_{mb} = 25 °C; Fig. 1 & T_{mb} = 25 °C; Fig. 2 & $[1]$ & V_{GS} = 10 V; T_{mb} = 25 °C; Fig. 2 & $[1]$ & V_{GS} = 10 V; T_{mb} = 100 °C; $Fig. 2 & V_{GS} = 10 V; T_{mb} = 25 °C; $Fig. 3 & $torage temperature & $ulsed; t_p < 10 μs; T_{mb} = 25 °C; $Fig. 3 & $torage temperature & $ulsed; t_p < 10 μs; T_{mb} = 25 °C; $Fig. 3 & $torage temperature & $ulsed; t_p < 10 μs; T_{mb} = 25 °C; $Fig. 3 & $ulsed; $ulsed;$	$\begin{tabular}{ c l l l l l l l l l l l l l l l l l $	$\begin{tabular}{ c c c c c } \hline I_{mb} = 25 °C; Fig.1 & $-$ 333 \\ \hline I_{rain} current & V_{GS} = 10 V; T_{mb} = 25 °C; $Fig.2 & $[1] $-$ 200 \\ \hline V_{GS} = 10 V; T_{mb} = 100 °C; $Fig.2 & $-$ 181 \\ \hline $Peak$ drain current & $pulsed; $t_p \le 10 \ μs; T_{mb} = 25 °C; $Fig.3 & $-$ 1049 \\ \hline $storage$ temperature & $-$55 $ 175 \\ \hline $junction$ temperature & $-$55 $ 175 \\ \hline $peak$ soldering \\ temperature & $-$55 $ 175 \\ \hline $peak$ soldering \\ temperature & $-$55 $ 175 \\ \hline $peak$ soldering \\ temperature & $-$55 $ 175 \\ \hline $peak$ soldering \\ temperature & $-$55 $ 175 \\ \hline $peak$ source current & T_{mb} = 25 °C & $-$ 260 \\ \hline $peak$ source current & $pulsed; $t_p \le 10 \ μs; T_{mb} = 25 °C & $-$ 1049 \\ \hline $gedness$ \\ \hline $non-repetitive drain-source avalanche energy $ I_D = 50 $A; V_{sup} $ $55 $V; R_{GS} = 50 Ω; $ V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; $t_p = 417 \ μs $ I_D = 25 $A; V_{sup} $ $55 $V; R_{GS} = 50 Ω; $ V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; $t_p = 1.98 \ s $non-repetitive avalanche V_{sup} $ $55 $V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; $12 $ $-$ 115 \\ \hline $non-repetitive avalanche V_{sup} $ $55 $V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; $20 $ C; $20 $ $-$ 115 \\ \hline $non-repetitive avalanche V_{sup} $ $55 $V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; $20 $ C; $20 $ C; $20 $ $-$ 115 \\ \hline $non-repetitive avalanche V_{sup} $ $55 $V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; $20 C; $20 $ $-$ 115 \\ \hline $non-repetitive avalanche V_{sup} $ $55 $V; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; $20 C; $20 $ $-$ 115 \\ \hline $non-repetitive avalanche V_{sup} $ $55 $V; V_{GS} = 10 V; $T_{j(init)}$ = $25 °C; $20 $ C; 2

[1] 200A Continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] Protected by 100% test

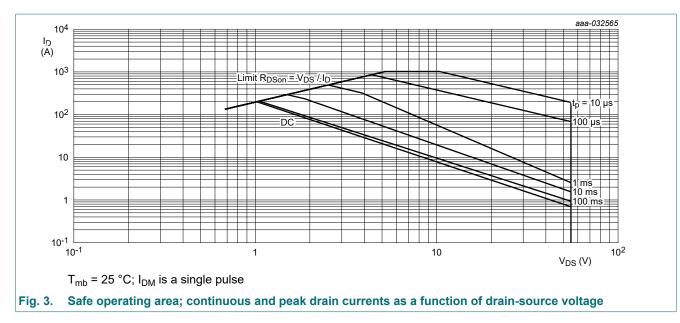




(1) 200A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature

Product data sheet



Thermal characteristics 9.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 4</u>	-	0.33	0.45	K/W
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance from	<u>Fig. 5</u>	-	42	-	K/W
	Fig. 6	-	85	-	K/W	

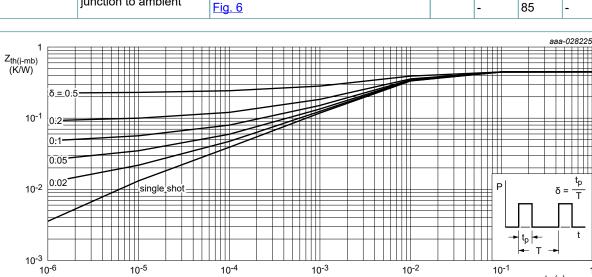


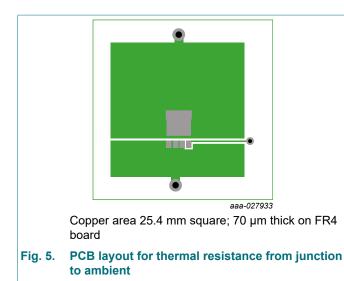
Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

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t_p (s)

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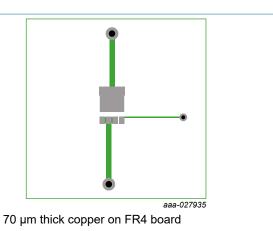


Fig. 6. PCB layout with minimum footprint for thermal resistance from junction to ambient

10. Characteristics

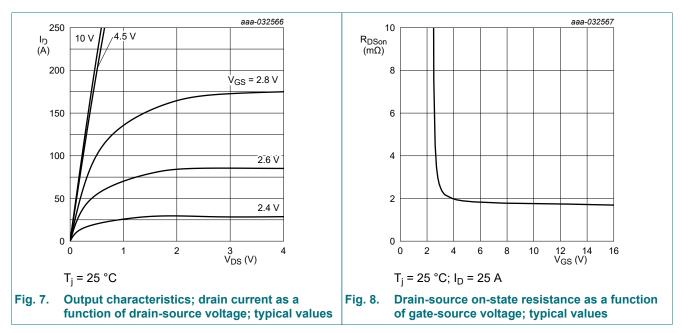
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	teristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	55	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	49.5	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C	1.2	1.62	2.2	V
$\Delta V_{GS(th)} / \Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	-4.6	-	mV/K
I _{DSS}	drain leakage current	V _{DS} = 44 V; V _{GS} = 0 V; T _j = 25 °C	-	0.01	1	μA
		V _{DS} = 44 V; V _{GS} = 0 V; T _j = 125 °C	-	3.5	-	μA
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 10	-	1.63	2.1	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 150 °C; Fig. 11	-	-	4.3	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 25 °C; Fig. 10	-	1.83	2.4	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 150 °C; Fig. 11	-	-	4.9	mΩ
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	0.52	1.3	3.3	Ω
Dynamic cha	racteristics					
Q _{G(tot)}	total gate charge	$I_{D} = 25 \text{ A}; V_{DS} = 27 \text{ V}; V_{GS} = 4.5 \text{ V};$ Fig. 12; Fig. 13	-	54	84	nC
		I_D = 25 A; V_{DS} = 27 V; V_{GS} = 10 V; Fig. 12; Fig. 13	-	119	184	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	64	-	nC

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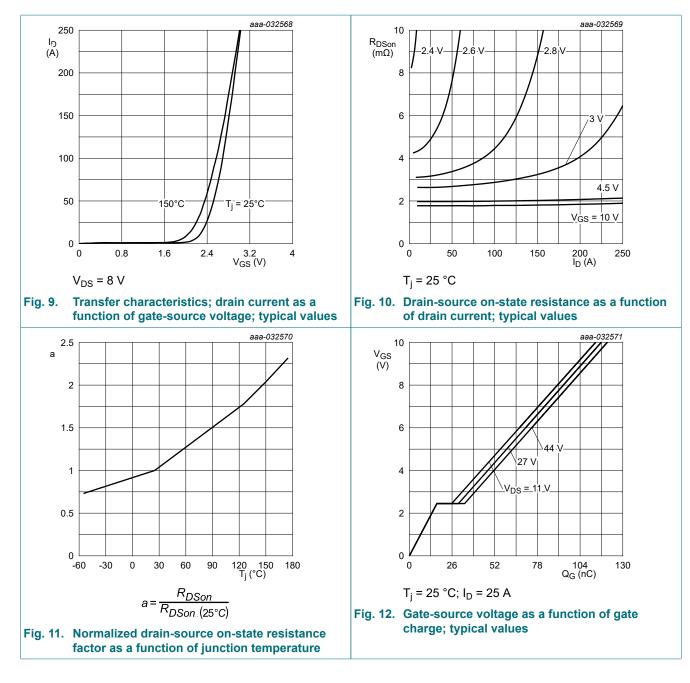
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q _{GS}	gate-source charge	I _D = 25 A; V _{DS} = 27 V; V _{GS} = 4.5 V;		-	17	26	nC
Q _{GS(th)}	pre-threshold gate- source charge	Fig. 12; Fig. 13		-	12	18	nC
Q _{GS(th-pl)}	post-threshold gate- source charge	-		-	5.8	8.8	nC
Q _{GD}	gate-drain charge			-	14	31	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 27 V; <u>Fig. 12</u> ; <u>Fig. 13</u>		-	2.5	-	V
C _{iss}	input capacitance	V _{DS} = 27 V; V _{GS} = 0 V; f = 1 MHz;		-	8109	11353	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>		-	704	986	pF
C _{rss}	reverse transfer capacitance			-	226	542	pF
t _{d(on)}	turn-on delay time	V_{DS} = 27 V; R _L = 1.1 Ω; V _{GS} = 4.5 V; R _{G(ext)} = 5 Ω		-	39	-	ns
t _r	rise time			-	38	-	ns
t _{d(off)}	turn-off delay time			-	60	-	ns
t _f	fall time	-		-	28	-	ns
Q _{oss}	output charge	V _{GS} = 0 V; V _{DS} = 27 V; f = 1 MHz; T _j = 25 °C		-	41	-	nC
Source-dra	in diode						
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 15</u>		-	0.75	1	V
t _{rr}	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$		-	36	-	ns
Q _r	recovered charge	V _{DS} = 27 V; <u>Fig. 16</u>	[1]	-	36	-	nC
t _a	reverse recovery rise time			-	21	-	ns
t _b	reverse recovery fall time			-	14	-	ns

[1] includes capacitive recovery



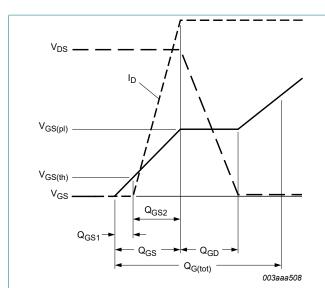
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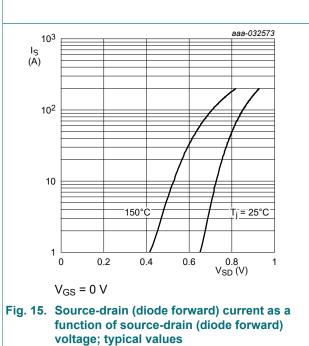


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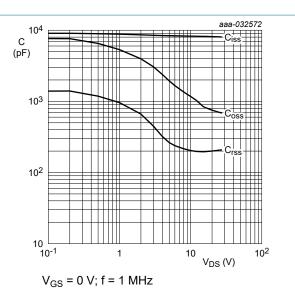
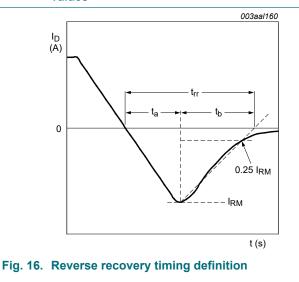


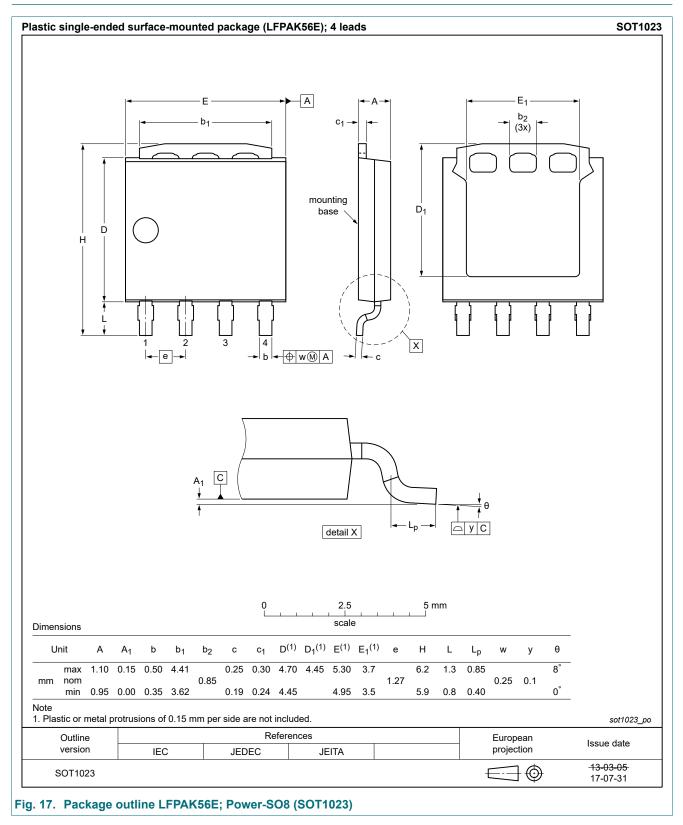
Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



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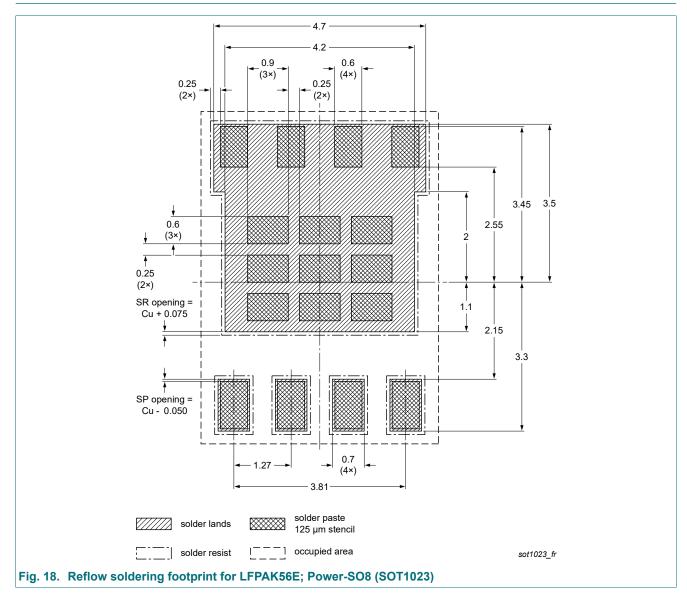
Product data sheet

11. Package outline



Product data sheet

12. Soldering



Product data sheet

13. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

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